



Serial No. 10/588,007

IN THE UNITED STATES PATENTS AND TRADEMARK OFFICE

KPO-003

Applicant : Naoto Hirosaki et al.  
Title : LIGHT EMITTING ELEMENT AND LIGHTING INSTRUMENT  
Serial No. : 10/588,007  
Filed : August 17, 2006  
Group Art Unit : 2879  
Examiner : Peter J. Macchiarolo

Hon. Commissioner for Patents  
P.O. Box 1450, Alexandria, VA 22313-1450

DECLARATION UNDER RULE 132

Sir:

We, Naoto Hirosaki, Ken Sakuma, Kyota Ueda and Hajime Yamamoto having a post office address at c/o National Institute for Materials Science of 2-1, Sengen 1-chome, Tsukuba-shi, Ibaraki 305-0047, Japan, declare, as follow:

We are inventors of the above application.

$\text{CaAlSiN}_3$  defined in claim 1 of the invention and  $\text{Ca-}\alpha\text{-sialon}$  disclosed in US Publication No. US 2003/0030368 are registered in JCPDS Card No. 39-0747 and JCPDS Card No. 33-0261, respectively, and the crystal structures are known.

The JCPDS Cards and their translations are attached herewith to show the differences of the crystal structures of  $\text{CaAlSiN}_3$  and  $\text{Ca-}\alpha\text{-sialon}$ .

We hereby declare that all statements made herein of our own knowledge are true, and that all statements made on information and belief are believed to be true, and further that these statements

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were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Date February 2, 2009 By Naoto Hirosaki  
Naoto Hirosaki

Date February 11, 2009 By Ken Sakuma  
Ken Sakuma

Date Feb. 3, 2009 By Kyota Ueda  
Kyota Ueda

Date Feb. 5, 2009 By Hajime Yamamoto  
Hajime Yamamoto

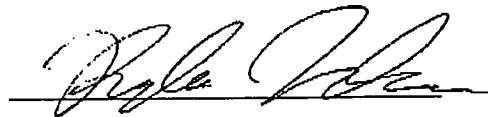
IN THE U.S. PATENT OFFICE

Applicant : Naoto Hiroasaki et al.  
Title : LIGHT EMITTING ELEMENT AND LIGHTING INSTRUMENT  
Serial No. : 10/588,007  
Filed : August 17, 2006

VERIFICATION OF TRANSLATION

Sir:

I, Kyoko Nakamura, residing at 2211 Whiteoaks Dr., Alexandria, VA 22306, declare that I am fluent in Japanese and English, and that herewith submitted English translations of JCPDS Card No. 39-0747 and JCPDS Card No. 33-0261 are true and accurate literal translations.



Date: January 29, 2009

**Name and chemical formula**

Reference code: 39-0747  
PDF index name: Calcium Aluminum Silicon Nitride  
Empirical rule:  $\text{AlCaN}_3\text{Si}$   
Chemical formula:  $\text{CaAlSiN}_3$

**Crystal structural parameter**

Crystal system: Orthorhombic system  
Space group: C

a (Å): 5.6290  
b (Å): 9.5840  
c (Å): 4.9860  
Alpha (°): 90.0000  
Beta (°): 90.0000  
Gamma (°): 90.0000

Volume of unit cell: 268.99  
RIR: -

**Subfile and quality**

Subfile: Inorganic  
Alloy, metal or intermetallic  
Quality: Indexed (I)

**Comment**

Specimen preparation: E-phase. Decomposition product of M-phase ( $2\text{CaO}:\text{Si}_3\text{N}_4:\text{AlN}$ ) by hot pressing at 1500 C for 1 hour. Accompanied by AlN phase.

**Reference**

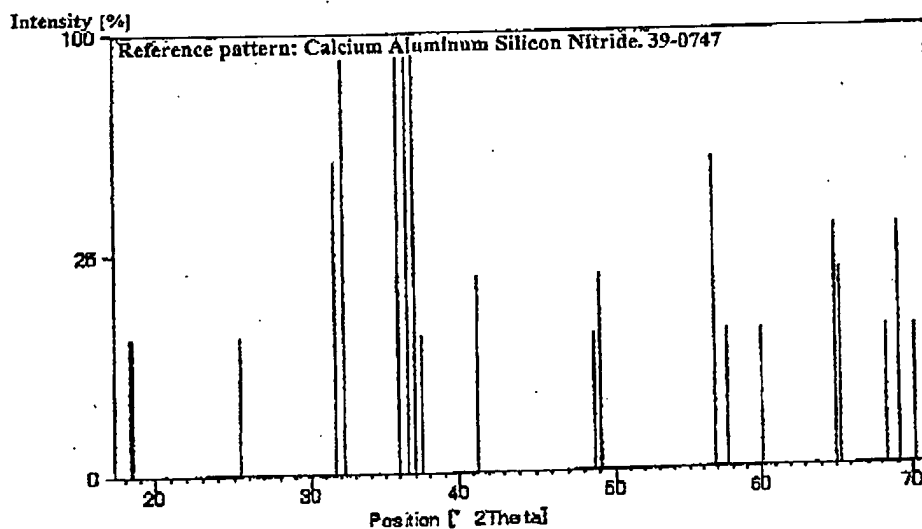
Priority reference: Huang, Z., Sun, W., Yan, D., *J. Mater. Sci. Lett.*, 4, 255, (1985)

**Peak list**

No.	h	k	l	d (Å)	I (%)
-----	---	---	---	-------	-------

1	1	1	0	4.83900	10.0
2	0	2	0	4.78900	10.0
3	1	1	1	3.48200	10.0
4	2	0	0	2.81900	50.0
5	1	3	0	2.77300	100.0
6	0	0	2	2.49500	100.0
7	2	0	1	2.45300	100.0
8	1	3	1	2.42200	100.0
9	0	4	0	2.39400	10.0
10	2	2	1	2.18300	20.0
11	2	0	2	1.86600	10.0
12	1	3	2	1.85400	20.0
13	3	3	0	1.61800	50.0
14	0	6	0	1.59800	10.0
15	3	3	1	1.53900	10.0
16	2	0	3	1.43300	30.0
17	1	3	3	1.42600	20.0
18	2	2	3	1.37100	10.0
19	3	3	2	1.35600	30.0
20	2	6	1	1.33900	10.0

# Line pattern



**Name and chemical formula**

Reference code: 33-0261  
PDF index name: Calcium Aluminum Silicon Nitride Oxide  
Empirical rule:  $\text{Al}_{2.8}\text{Ca}_{0.8}\text{N}_{14.8}\text{O}_{1.2}\text{Si}_{9.2}$   
Chemical formula:  $\text{Ca}_{0.8}\text{Si}_{9.2}\text{Al}_{2.8}\text{O}_{1.2}\text{N}_{14.8}$

**Crystal structural parameter**

Crystal system: Hexagonal system  
Space group: P31c  
Space group No.: 159

a (Å): 7.8520  
b (Å): 7.8520  
c (Å): 5.7090  
Alpha (°): 90.0000  
Beta (°): 90.0000  
Gamma (°): 120.0000

Calculation density: 3.23  
Actual measurement density: 3.21  
Volume of unit cell: 304.83  
Z: 1.00

RIR:

**Subfile and quality**

Subfile: Inorganic  
Corrosion  
Quality: Indexed (I)

**Comment**

Color: Gray

Comment:  $\alpha'$  silafons have the general composition  $\text{M}_x\text{Si}_{12-p}\text{Al}_p\text{O}_n\text{N}_{16-n}$  where  $\text{M}=\text{Li}, \text{Ca}, \text{Y}$  and  $0 \leq x \leq 2$ . They are structurally related to  $\alpha$ -silicon nitride, with M atoms occupying large interstices in the silicon-nitrogen framework. Aluminium replaces silicon and some oxygen replaces nitrogen in order to preserve charge balance.

Specimen preparation:

CaO,  $3\text{Si}_3\text{N}_4$ ,  $3\text{AlN}$  heated in nitrogen at 1750 C for 15 minutes.

Reference

Priority reference:

Thompson, D., *Private Communication*

Unit cell:

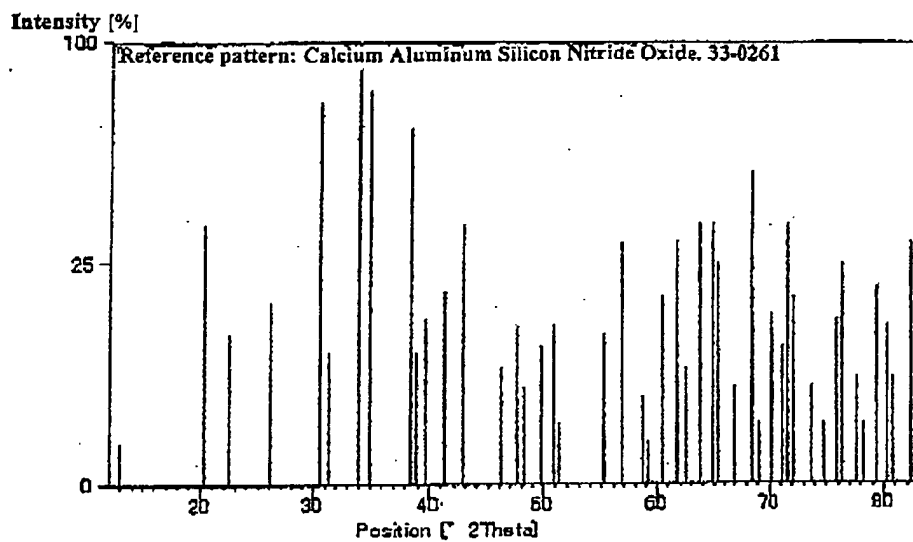
Hampshire, S. et al., *Nature (London)*, 274, 880, (1978)

Peak list

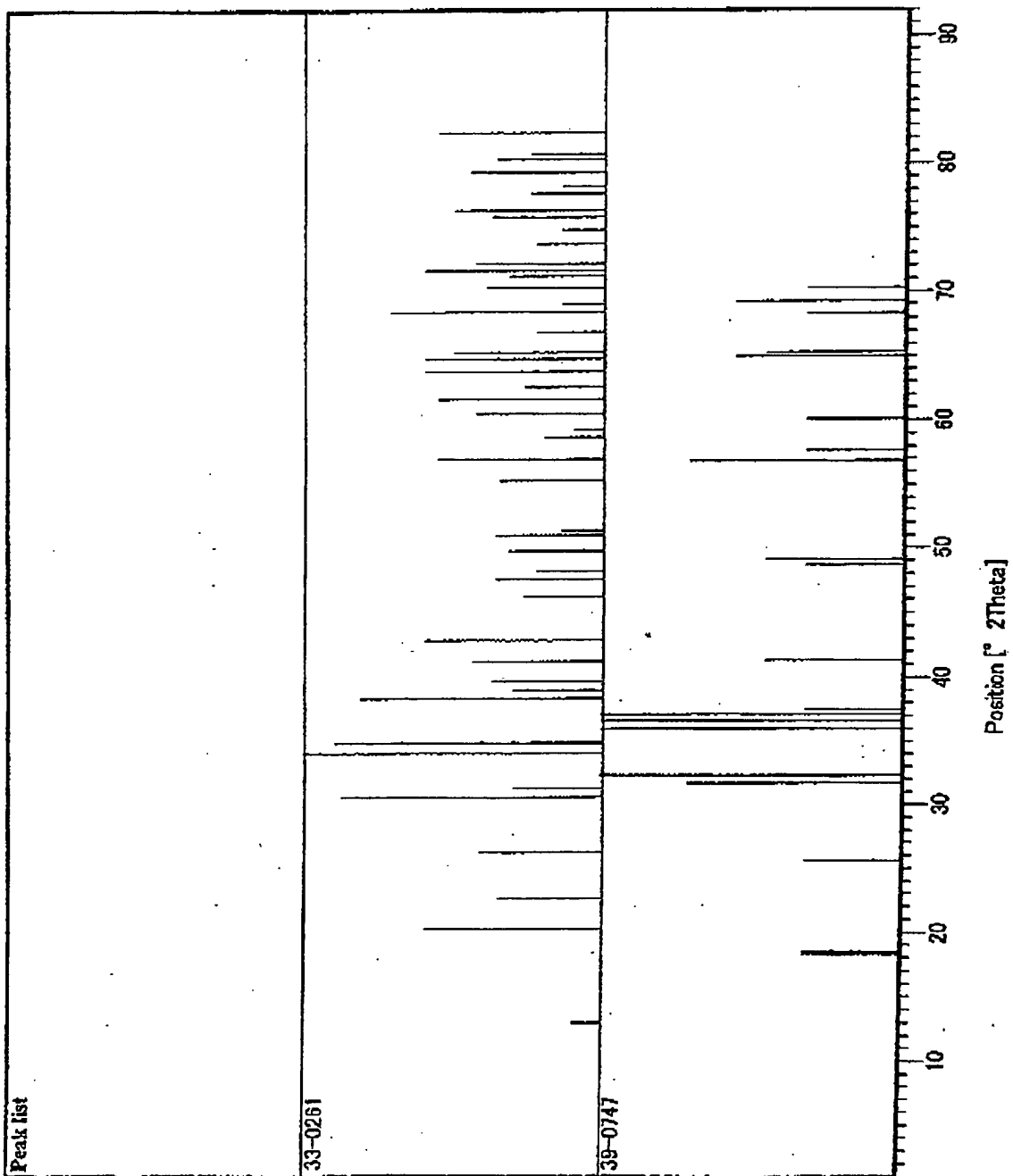
No.	h	k	l	d (Å)	I (%)
1	1	0	0	6.80200	1.0
2	1	0	1	4.37300	35.0
3	1	1	0	3.92800	12.0
4	2	0	0	3.40100	17.0
5	2	0	1	2.92100	75.0
6	0	0	2	2.85800	9.0
7	1	0	2	2.63200	100.0
8	2	1	0	2.56900	80.0
9	2	1	1	2.34300	65.0
10	1	1	2	2.30900	9.0
11	3	0	0	2.26700	14.0
12	2	0	2	2.18600	19.0
13	3	0	1	2.10600	35.0
14	2	2	0	1.96200	7.0
15	2	1	2	1.91000	13.0
16	3	1	0	1.88500	5.0
17	1	0	3	1.83200	10.0
18	3	1	1	1.79000	13.0
19	3	0	2	1.77700	2.0
20	2	0	3	1.66000	12.0
21	2	2	2	1.61700	30.0
22	3	1	2	1.57300	4.0
23	3	2	0	1.55800	1.0
24	2	1	3	1.52900	18.0
25	3	2	1	1.50400	30.0
26	4	1	0	1.48400	7.0
27	4	0	2	1.45700	35.0
28	4	1	1	1.43600	35.0
29	0	0	4	1.42700	25.0
30	1	0	4	1.39700	5.0
31	3	2	2	1.36900	50.0
32	5	0	0	1.35900	2.0
33	1	1	4	1.33900	15.0
34	5	0	1	1.32300	10.0
35	4	1	2	1.31600	35.0
36	3	3	0	1.30900	18.0
37	4	2	0	1.28500	5.0
38	4	0	3	1.26800	2.0
39	4	2	1	1.25400	14.0
40	2	1	4	1.24700	25.0
41	5	0	2	1.22800	6.0

42	5	1	0	1.22100	2.0
43	3	0	4	1.20700	20.0
44	5	1	1	1.19400	13.0
45	3	3	2	1.18900	6.0
46	4	1	3	1.17000	30.0

**Line pattern**







## 名前及び化学式

リファレンスコード: 39-0747  
PDFインデックス名: Calcium Aluminum Silicon Nitride  
経験則:  $\text{AlCaN}_3\text{Si}$   
化学式:  $\text{CaAlSiN}_3$

## 結晶構造パラメータ

結晶系: 斜方晶系  
空間群: C  
a (Å): 5.6290  
b (Å): 9.5840  
c (Å): 4.9860  
Alpha (°): 90.0000  
Beta (°): 90.0000  
Gamma (°): 90.0000  
単位胞の体積: 268.99  
RIR: -

## サブファイル及びクオリティ

サブファイル: Inorganic  
Alloy, metal or Intermetallic  
クオリティ: Indexed (I)

## コメント

試料準備: E-phase. Decomposition product of M-phase ( $2\text{CaO}:\text{Si}_3\text{N}_4:\text{AlN}$ ) by hot pressing at 1500 C for 1 hour. Accompanied by AlN phase.

## リファレンス

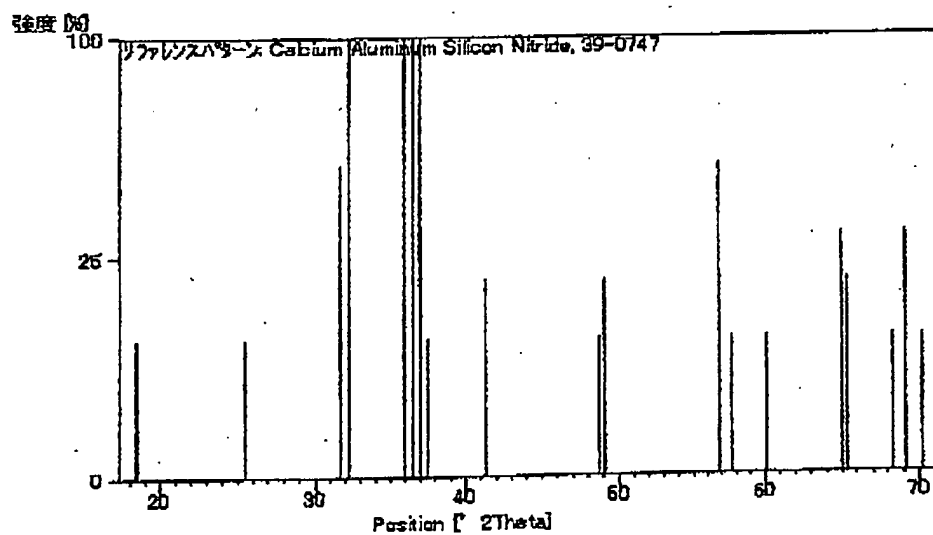
優先リファレンス: Huang, Z., Sun, W., Yan, D., *J. Mater. Sci. Lett.*, 4, 255, (1985)

## ピークリスト

No.	h	k	l	d (Å)	I (%)
-----	---	---	---	-------	-------

1	1	1	0	4.83900	10.0
2	0	2	0	4.78900	10.0
3	1	1	1	3.48200	10.0
4	2	0	0	2.81900	50.0
5	1	3	0	2.77300	100.0
6	0	0	2	2.49500	100.0
7	2	0	1	2.45300	100.0
8	1	3	1	2.42200	100.0
9	0	4	0	2.39400	10.0
10	2	2	1	2.18300	20.0
11	2	0	2	1.86600	10.0
12	1	3	2	1.85400	20.0
13	3	3	0	1.61800	50.0
14	0	6	0	1.59800	10.0
15	3	3	1	1.53900	10.0
16	2	0	3	1.43300	30.0
17	1	3	3	1.42600	20.0
18	2	2	3	1.37100	10.0
19	3	3	2	1.35600	30.0
20	2	6	1	1.33900	10.0

# ラインパターン



## 名前及び化学式

リファレンスコード:	33-0281
PDFインデックス名:	Calcium Aluminum Silicon Nitride Oxide
経験則:	$\text{Al}_{2.0}\text{Ca}_{0.8}\text{N}_{14.8}\text{O}_{1.2}\text{Si}_{9.2}$
化学式:	$\text{Ca}_{0.8}\text{Si}_{9.2}\text{Al}_{2.8}\text{O}_{1.2}\text{N}_{14.8}$

## 結晶構造パラメータ

結晶系:	立方晶系
空間群:	P31c
空間群No.:	159

a (Å):	7.8520
b (Å):	7.8520
c (Å):	5.7090
Alpha (°):	90.0000
Beta (°):	90.0000
Gamma (°):	120.0000

計算密度:	3.23
実測密度:	3.21
単位胞の体積:	304.83
Z:	1.00

RIR:

## サブファイル及びクオリティ

サブファイル:	Inorganic
クオリティ:	Corrosion Indexed (1)

## コメント

カラー:	Gray
コメント:	$\alpha'$ silicons have the general composition $\text{M}_x\text{Si}_{12-2x}\text{Al}_x\text{O}_x\text{N}_{18-2x}$ where $\text{M}=\text{Li}, \text{Ca}, \text{Y}$ and $0 \leq x \leq 2$ . They are structurally related to $\alpha$ -silicon nitride, with M atoms occupying large interstices in the silicon-nitrogen framework. Aluminium replaces silicon and some oxygen replaces nitrogen in order to preserve charge balance.

試料準備:

CaO,  $3\text{Si}_3\text{N}_4$ ,  $3\text{AlN}$  heated in nitrogen at 1750 C for 15 minutes.

リファレンス

優先リファレンス:

Thompson, D., *Private Communication*

単位胞:

Hampshire, S. et al., *Nature (London)*, 274, 880. (1978)

ピークリスト

No.	h	k	l	d (Å)	I (%)
1	1	0	0	6.80200	1.0
2	1	0	1	4.37300	35.0
3	1	1	0	3.92800	12.0
4	2	0	0	3.40100	17.0
5	2	0	1	2.92100	75.0
6	0	0	2	2.85800	9.0
7	1	0	2	2.63200	100.0
8	2	1	0	2.56900	80.0
9	2	1	1	2.34300	65.0
10	1	1	2	2.30900	9.0
11	3	0	0	2.26700	14.0
12	2	0	2	2.18600	19.0
13	3	0	1	2.10600	35.0
14	2	2	0	1.96200	7.0
15	2	1	2	1.91000	13.0
16	3	1	0	1.88500	5.0
17	1	0	3	1.83200	10.0
18	3	1	1	1.79000	13.0
19	3	0	2	1.77700	2.0
20	2	0	3	1.66000	12.0
21	2	2	2	1.61700	30.0
22	3	1	2	1.57300	4.0
23	3	2	0	1.55800	1.0
24	2	1	3	1.52900	18.0
25	3	2	1	1.50400	30.0
26	4	1	0	1.48400	7.0
27	4	0	2	1.45700	35.0
28	4	1	1	1.43600	35.0
29	0	0	4	1.42700	25.0
30	1	0	4	1.39700	5.0
31	3	2	2	1.36900	50.0
32	5	0	0	1.35900	2.0
33	1	1	4	1.33900	15.0
34	5	0	1	1.32300	10.0
35	4	1	2	1.31600	35.0
36	3	3	0	1.30900	18.0
37	4	2	0	1.28500	5.0
38	4	0	3	1.26800	2.0
39	4	2	1	1.25400	14.0
40	2	1	4	1.24700	25.0
41	5	0	2	1.22800	6.0

42	5	1	0	1.22100	2.0
43	3	0	4	1.20700	20.0
44	5	1	1	1.19400	13.0
45	3	3	2	1.18900	6.0
46	4	1	3	1.17000	30.0

ラインパターン

